

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS:**

Claims 1-10 (canceled)

Claim 11 (currently amended) A component of semiconductor processing equipment, the component comprising an aluminum substrate and a ceramic layer of cerium oxide containing ceramic material on the substrate and forming an outermost surface of the component, wherein the cerium oxide containing ceramic material comprises (a) consists essentially of one or more cerium oxides as the single largest constituent thereof or (b) consists essentially of one or more cerium oxides as the single largest constituent thereof and an oxide of an element of the lanthanide series.

Claims 12-13 (canceled)

Claim 14 (currently amended) The component according to Claim # 11, wherein the aluminum substrate has an anodized surface and the ceramic layer is disposed on the anodized surface.

Claim 15 (currently amended) The component according to Claim 11, wherein the ceramic layer has a thickness in a range from about 0.001 to 0.050 inches.

Claim 16 (original) The component according to Claim 11, wherein the component comprises a part exposed to a plasma environment or a part exposed to bias voltages associated with a plasma environment.

Claim 17 (currently amended) ~~The component according to Claim 11, wherein the component comprises a bulk part consisting essentially of the cerium oxide containing ceramic material. A component of semiconductor processing equipment, the component comprising a bulk part consisting essentially of a cerium oxide containing ceramic material, the component being selected from the group consisting of a plasma chamber wall, a chamber liner, a gas distribution plate, a gas ring, a pedestal, a dielectric window, an electrostatic chuck, and a focus ring, and the cerium oxide containing ceramic material comprising one or more cerium oxides as the single largest constituent thereof.~~

Claim 18 (currently amended) ~~The component according to Claim 11, wherein the component is selected from the group consisting of a plasma chamber wall, a chamber liner, a gas distribution plate, a gas ring, a pedestal, a dielectric window, an electrostatic chuck and a focus ring. A component of semiconductor processing equipment, the component comprising a cerium oxide containing ceramic material forming an outermost~~

surface of the component, the component being selected from the group consisting of a plasma chamber wall, a chamber liner, a gas distribution plate, a gas ring, a pedestal, a dielectric window, an electrostatic chuck, and a focus ring, and the cerium oxide containing ceramic material comprising one or more cerium oxides as the single largest constituent thereof, wherein (a) the component is a bulk part consisting essentially of the cerium oxide containing ceramic material or (b) the cerium oxide containing ceramic material comprises a ceramic layer on a ceramic substrate.

Claim 19 (original) The component according to Claim 11, wherein the cerium oxide comprises Ce(III) oxide and/or Ce(IV) oxide.

Claims 20-23 (canceled)

Claim 24 (new) The component according to Claim 11, wherein the component is selected from the group consisting of a plasma chamber wall, a chamber liner, a gas distribution plate, a gas ring, a pedestal, a dielectric window, an electrostatic chuck and a focus ring.

Claim 25 (new) The component according to Claim 17, wherein the component comprises a part exposed to a plasma environment or a part exposed to bias voltages associated with a plasma environment.

Claim 26 (new) The component according to Claim 17, wherein the cerium oxide comprises Ce(III) oxide and/or Ce(IV) oxide.

Claim 27 (new) The component according to Claim 18, wherein the cerium oxide containing ceramic material comprises a ceramic layer on a substrate.

Claim 28 (new) The component according to Claim 27, wherein the substrate comprises aluminum.

Claim 29 (new) The component according to Claim 28, wherein the aluminum substrate has an anodized surface and the ceramic layer is disposed on the anodized surface.

Claim 30 (new) The component according to Claim 18, wherein the ceramic layer has a thickness in a range of from about 0.001 to 0.050 inches.

Claim 31 (new) The component according to Claim 18, wherein the component comprises a part exposed to a plasma environment or a part exposed to bias voltages associated with a plasma environment.

Claim 32 (new) The component according to Claim 18, wherein the cerium oxide comprises Ce(III) oxide and/or Ce(IV) oxide.

Claim 33 (new) The component according to Claim 18, wherein the component is the bulk part.

Claim 34 (new) The component according to Claim 18, wherein the cerium oxide containing ceramic material comprises the ceramic layer on the ceramic substrate.

Claim 35 (new) The component according to Claim 34, wherein the substrate is selected from the group consisting of alumina, silicon carbide, silicon nitride, boron carbide, and boron nitride.

Claim 36 (new) The component according to Claim 34, wherein the substrate is a polymeric material.